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REMARKS

Claims 1-8, 10-13 and 23-38 are all the claims presently pending in the application.

Claims 27, 29, 31, 33, 35, and 37 stand rejected upon informalities (e.g., 35 U.S.C. § 112, first paragraph), claims 5-8, 23 and 24 stand rejected upon informalities (e.g., 35 U.S.C. § 112, second paragraph), and claims 1-3, 23, 4-8, 10, 12, 24, 13, 25, 26, 27-30, and 31-38 stand rejected on prior art grounds.

With respect to the prior art rejections, claims 1-8, 10-13 and 23-38 stand rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 28-31 of Ajmera et al. (U.S. Patent No. 6,503,833 B1). Claims 1-8, 10-13, and 23-38 stand rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-50 of Cabral, Jr., et al. (U.S. Patent No. 6,444,578 B1). Finally, the Examiner indicates that claims 1-8, 10-13, and 23-38 appear to conflict with claims 1-30 of parent application No. 09/569,306.

Further, claims 1-3, 23, 4-6, 8, 12, 24, 13, 25 and 26 stand rejected under 35 U.S.C. § 102(b) as being anticipated by Maa et al. (U.S. Patent No. 5,830,775). Claim 7 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over Maa in view of Kanamori (Patent Application Publication US 2002/0009856 A1). Claims 10, 31 and 32 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Maa in view of Cabral, Jr., et al. (U.S. Patent No. 5,828,131).

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These rejections are respectfully traversed in view of the following discussion.

It is noted that the claim amendments herein are made only for more particularly pointing out the invention for the Examiner, and not for distinguishing the invention over the prior art, narrowing the claims, or for any statutory requirements of patentability.

Indeed, it is noted that, while Applicant submits that Maa (nor any of the other prior art of record), either alone or in combination, fails to teach any of "a metal containing silicon" or "a metal alloy", to speed prosecution, Applicant has deleted "metal alloy" from the claims, thereby to pass the present claims to issue.

Applicant reserves the opportunity to file a Divisional Application directed to such subject matter later, as again Applicant submits that a reasonable reading of Maa (either alone or in combination with any of the other prior art of record) would not have reasonably taught or suggested a "metal alloy" in the context of the present invention.

Further, it is noted that, notwithstanding any claim amendments made herein, Applicant's intent is to encompass equivalents of all claim elements, even if amended herein or later during prosecution.

Entry of this Amendment is believed proper since no new issues are being presented to the Examiner which would require further consideration and/or search. Indeed, the claim amendments above narrow the issues on appeal. Specifically and as mentioned above, the claims have been amended to more particularly point out the invention.

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I. THE CLAIMED INVENTION

Applicant's invention, as exemplarily disclosed and claimed (e.g., see independent claim 1), is directed to a method for fabricating a silicide for a semiconductor device, which includes depositing a metal containing silicon on a silicon substrate, reacting the metal containing silicon to form a first silicide phase, etching any unreacted metal containing silicon, depositing a silicon cap layer over the first silicide phase, reacting the silicon cap layer to form a second silicide phase, for the semiconductor device, and etching any unreacted silicon from the silicon cap layer.

Independent claims 4, 10, 13, 25, and 26 recite somewhat similar methods, but with some different limitations.

With such features and as mentioned previously, a reaction of a metal (e.g., Co in an exemplary embodiment, but other metals will be similarly operable as claimed and as clearly described in the specification) containing silicon, to initially form Co_2Si , minimizes the silicon consumption of the thin SOI film (or bulk silicon) substrate.

The consumption of the thin SOI film is additionally reduced by the deposition of a silicon (or poly-silicon in a non-limiting exemplary variation of the invention) film on the Co_2Si .

Such exemplary features are not taught or suggested by any other prior art of record, either alone or in combination.

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II. THE 35 U.S.C. §112, SECOND PARAGRAPH, REJECTION

While Applicant submits that the claims are clear to one of ordinary skill in the art to recognize the metes and bounds of the invention, to speed prosecution, claims 5-7 have been amended in a manner believed fully responsive to the Examiner's criticisms.

Thus, claims 5-7 are believed to be clear and sufficiently definite to one of ordinary skill in the art to know the metes and bounds of the invention.

In view of the foregoing, reconsideration and withdrawal of this rejection are respectfully requested.

III. THE PRIOR ART REJECTIONS

A. The §102(b) Rejection Based on Maa et al.

Regarding the rejection of claims 1-3, 4-6, 8, 12, 13, and 23-26, Maa et al. (U.S. Patent No. 5,830,775) is clearly deficient.

First, it is noted that the Examiner clearly admits (e.g., see Item No. 10 on page 6 of the Office Action, etc.) that Maa et al. fails to teach or suggest "*a ... metal alloy containing silicon was deposited to form the silicide*". As the Examiner well-knows, for a §102 rejection, all

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limitations in the claim must be found, explicitly or inherently, within the four corners of a single reference. Here, Maa fails.

Independent claims 1, 4, 25, and 26 each clearly require a "metal containing silicon." (emphasis Applicant's). Thus, on its face, the Examiner's rejection is flawed.

Maa does not teach or suggest the use of a metal-silicon alloy as silicidation material.

Indeed, Maa teaches away from such a claimed feature.

Maa defines a "silicidation material" as one of pure metals such as "Co, Ti, Ni, W, Pt, Pd, Mo and Ta" (e.g., see Col. 4, line 63 of Maa). Maa suggests the use of a multi-layer stack "*[l]ayer 80 is either a uniform layer of a single metal, for example cobalt, or alternatively, is made up of more than one layer of silicidation material. For example, layer 80 might include a lower layer of Ti and upper layer of Co.*" (e.g., see Col. 4, line 64 to Col. 5, line 1 of Maa et al.). In this regard, Maa does not even teach a metal alloy, let alone the use of a metal-silicon alloy. In fact, Maa does not propose, teach, or suggest the use of any alloys such as metal alloys, but rather clearly teaches that a layered structure of pure metals is desirable.

Hence, Maa defines a "silicidation material" as one of pure metals such as "Co, Ti, Ni, W, Pt, Pd, Mo and Ta" (e.g., see Col. 4, line 63 of Maa). Maa suggests the use of a multi-layer stack "*[l]ayer 80 is either a uniform layer of a single metal, for example cobalt, or alternatively, is made up of more than one layer of silicidation material. For example, layer 80 might include a lower layer of Ti and upper layer of Co.*" (e.g., see Col. 4, line 64 to Col. 5, line 1 of Maa et al.).

Hence, Maa teaches only silicidation materials as being pure metals (i.e., refractory metals or

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noble metals), and with each being formed as a layer. There is no teaching or suggestion of a metal alloy, let alone "a metal containing silicon", as in the claimed invention.

Thus, Maa's layer 80 (or a multilayer stack of metal layers) does not teach, suggest or represent an alloy as in the invention, let alone a metal-silicon alloy.

Again, Maa clearly teaches only that a layered structure of metals (e.g., pure metals or a stack of pure metals) is desirable. A layered stack structure of metals is not an alloy. In this regard, the Examiner is ignoring the plain language and plain meaning of the claim limitations. Indeed, Webster's New World Dictionary, Third College Edition, Simon & Schuster, (New York, 1988) defines an "alloy" as "... *2. a substance that is a mixture, as by fusion, of two or more metals, or of a metal and something else...*" (See Exhibit 1 attached hereto). It is noted that in doing a chemical analysis of an alloy, one typically finds a first percent of a first metal and a second percent of a second material (metal or another material). A layered stack of pure metals does not have such an alloyed structure.

Thus, in attempting to apply Maa's layered stack 80 against the claimed "alloy", the Examiner is clearly ignoring the plain meaning of "alloy" in the claims.

Notwithstanding the above, Applicant has made the claimed distinction even more clear by reciting the "metal containing silicon". Clearly, Maa does not teach or suggest such a structure.

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Thus, independent claims 1, 4, 13, 25, and 26, which clearly recite depositing "*a metal containing silicon*" are clearly not taught or suggested by Maa et al., and thus are clearly patentable over Maa et al., either alone or in combination.

Regarding dependent claims 2, 3, 5, 6, 8, 12, 23, 24, 27-30, and 33-38, these claims are patentable not only by virtue of their dependency from the above independent claims, but also for the additional limitations which they recite.

That is, first, with regard to dependent claims 23 and 24, Maa does not teach the use of a first forming phase as in the claimed invention.

Maa admits, in the disclosure thereof, that "*the compound form in 90 in Fig. 5 may contain both Co_2Si and CoSi* " (col. 5, line 30), with the reason being the narrow temperature window in which this first forming phase exists. This is precisely why Maa's disclosure avoids the term "metal-rich phase" when referring to 90 and instead named 90 as a "silicon deficient silicide".

Even assuming arguendo that Maa realized that it is preferable to form Co_2Si rather than CoSi to reduce silicon consumption from the substrate (Col. 5, lines 49-52), Maa only discusses the "likelihood of forming Co_2Si being improved if the temperature range is between 450C to 500C" (Col. 5, lines 55-57). However, Maa provides no sound method by which only Co_2Si is obtained from such a process. Indeed, Maa avoids the term "metal-rich phase" and uses the term "silicon deficient silicide".

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It is noted that, contrary to the Examiner's comments on page 6 of the present Office Action, a clear reading of page 6 of the previous Amendment will reveal that Applicant did not "contradict" himself in the "Remarks" portion. Applicant neither "admitted" that Maa "does not form Co₂Si" nor that Maa teaches "mak[ing] Co₂Si". As is clear from page 6 of the June 13, 2003, Amendment, Applicant discussed that Maa fails to teach or suggest a method of forming Co₂Si.

Thus, Maa merely mentions that Co₂Si may be preferable, but teaches or suggests no method of getting there, and certainly not with the clear, unique, and unobvious combination of process steps of the present invention.

In essence, even if Maa may realize the it is preferable to form Co₂Si (a metal-rich phase), Maa is merely indicating that "it would be nice to do this, but I don't know how to do it".

To draw a simple analogy, many researchers, prior to the invention of the elevator, would probably have desired to descend a 10-story building effortlessly and safely, but the options included using a rope or jumping, none of which would reasonably have been taken as anticipating or rendering obvious the clear structure of the elevator.

Thus, Maa teaches no method for obtaining Co₂Si. He merely discloses that there may be an incidental chance of obtaining Co₂Si (presumably if many hundreds (or thousands) of wafers are processed) and that such would be preferable over CoSi. Again, there is no description, disclosure or suggestion of how to form the Co₂Si phase. There is no road map, let alone clear

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method steps (and certainly none for one of ordinary skill in the art), provided by Maa of how to get to the Co_2Si phase.

Indeed, when discussing the formation of the first phase (CoSi), Maa discloses that it may be a mixture of CoSi and Co_2Si , because Maa has no way to control it and has no control of what phase will form. This is the reason why the industry has not used the Co_2Si phase, because it has a very narrow temperature formation window. In contrast, the invention provides a clear, reliable method of producing (e.g., how to get to) the second phase (Co_2Si), and then forms a silicon cap thereover for the purpose of reducing silicon consumption, as discussed above.

In complete and fundamental contrast, the claimed invention has clear process steps utilizing a metal containing silicon as a way to obtain, for example, Co_2Si (and as defined in some of the present claims, as the "first forming phase").

Moreover, the incorporation of silicon into the metal reduces further the silicon consumption from the wafer already at the formation of the Co_2Si phase. None of these exemplary features is taught or suggested by Maa.

Finally, for the record, the Examiner's position regarding Maa depositing a "metal alloy" is clearly erroneous.

Indeed and at the expense of being redundant, referring to page 4 of the Office Action, Applicant points out that Maa does not deposit a metal alloy layer 80, but instead deposits a pure metal layer or a stack of pure metals. Maa does not teach or suggest forming a first metal rich silicide 90, but instead teaches a "silicon deficient silicide" that is "a phase of silicide having

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proportionally less silicon and more silicidation material than the more stable disilicide phase silicide" (see column 5, lines 14-16 of Maa; see also claim 1 of Maa).

Additionally, regarding dependent claims 28, 30, 34, 36, and 38, the Examiner asserts on page 4 of the Office Action that "[r]egarding claims 28, 30, 34, 36, and 38 it is seen to be inherent that the metal-alloy extends the temperature window in which a silicide metal-rich phase exist ... In other words, the more metal that is present relative to silicon the longer the window. Consequently if an alloy absent silicon is used the window is larger then if silicon is present." Applicant reiterates the discussion from pages 7-8 of the previous Amendment, incorporated herein by reference.

That is, contrary to the Examiner's statements, the addition of silicon to the metal widens the temperature window. Thus, the Examiner's statement on page 4 of the Office Action that "in other words, the more metal that is present relative to silicon, the longer the window", is clearly incorrect. Indeed, it is just the opposite. Adding silicon widens the window, not shortens it.

Referring to the exemplary case of cobalt-silicon alloy, an alloy absent of silicon result in a window that is only 20 °C wide. With the addition of 20% silicon, thus forming a Co(0.8)-Si(0.2) alloy, the window opens up and is 100 °C wide. This is a major benefit of the invention, and is not at all appreciated by Maa.

Therefore, the use of a metal containing silicon is important for obtaining the first forming phase Co₂Si. Such is not taught or suggested anywhere within Maa et al.

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B. The §103(a) Rejections Based on Maa et al. In view of Kanamori, or Cabral et al.

Regarding the rejection of claim 7 based on Maa in view of Kanamori (Patent Application Publication US 2002/0009856 A1), and the rejection of claims 10, 31 and 32 based on Maa in view of Cabral, Jr., et al. (U.S. Patent No. 5,828,131), even assuming arguendo that Kanamori and/or Cabral et al. would have been combined with Maa et al., Kanamori and Cabral et al. clearly fail to make up for the above deficiencies of Maa et al.

Again, Kanamori discloses a method of fabricating a semiconductor device self-aligned silicide areas formed using a supplemental silicon overlayer. Such methods are completely and fundamentally different from that of the invention defined by dependent claim 7.

The invention defined by claim 7 (and its dependency from independent claim 4) is clearly distinguished from Maa and Kanamori by a metal containing silicon (e.g., $\text{Co}_x\text{Si}_{1-x}$; a metal-silicon mixture), rather than a pure metal, or a layered stack of pure metals.

As mentioned previously and above, the use of the metal-silicon alloy allows several important advantages of the claimed invention, over Maa and/or Kanamori, as discussed above.

First, in the case of the metal-silicon mixture, the metal-silicon mixture already contains some of the silicon required to form the silicide. Thus, less silicon is consumed from the substrate during the subsequent anneal. Indeed, none of the references teaches or suggests using such a metal-silicon mixture, let alone for the reason and purpose of the invention.

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Furthermore, as noted in the previous Amendment and as mentioned above, the use of the metal-silicon mixture is fundamental to the inventive method and is neither taught or suggested by Maa et al. and/or Kanamori for all of the reasons discussed on pages 8-9 of the June 13, 2003, Amendment incorporated herein by reference (see also the diffraction maps shown in Figures 2A and 2B of Exhibit I submitted with the Amendment on May 14, 2002, incorporated herein by reference).

As noted, at a temperature lower than about 440 °C, no reaction takes place, and only pure Co is measured. Then, when the temperature is increased, the Co₂Si phase forms and exists only within a narrow window of about 20 °C, after which the phase changes into CoSi.

The CoSi phase persists up to 625 °C where it changes into CoSi₂. Since the Co₂Si phase only exists in a very narrow, tight temperature window, it is very difficult to form (e.g., very unreliable and prone to error or being missed based on nonuniform doping of the substrate, etc.) and control, as noted above, and, in practice, the later phase (e.g., CoSi) is used in self-aligned silicide processes.

The bottom map (e.g., Figure 2B) shows the evolution of reacting a metal (e.g., Co) containing silicon, as in the claimed invention.

That is, Figure 2B shows the metal (e.g., Co)-silicide phases when a Co-silicon mixture having 20% silicon is used instead of pure Co. In this case, the Co₂Si phase exists over a large temperature window of more than 100 °C. This makes it possible to practice a self-aligned silicide process where the first phase is also the first forming phase (Co₂Si). As a result, much

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more reliable and easier manufacturing processes are possible since it is easier to stop on Co_2Si , etc. In other words, the invention allows much greater control in forming the Co_2Si , as described above. Then, annealing can be performed, etc. to go to CoSi , and finally to CoSi_2 .

Again, Applicant submits that such is not trivial to use the method above (including using the metal-silicon mixture), and thus, it is clear that Kanamori et al. does not make up for the deficiencies of Maa.

Regarding the rejection of independent claim 10 (and claims 31 and 32), similarly, to Kanamori, Cabral et al. does not make up for the deficiencies of Maa et al., discussed above and in the June 13, 2003, Amendment incorporated herein by reference. For the Examiner's convenience, such a discussion will be provided below.

Cabral et al. is addressing the issue of the high temperature anneal required to form the low resistivity C54 phase, and proposes a method for lowering the formation temperature. It is noted that this issue is rather specific to titanium silicide and does not apply to all silicides in general.

Cabral et al. is addressing the issue of the high temperature anneal required to form the low resistivity C54 phase, and proposes a method for lowering the formation temperature. Again, it is noted that this issue is rather specific to titanium silicide and does not apply to all silicides in general.

Specifically, Cabral proposes depositing a Ti film over a refractory metal such as Ta, Nb, Mo, or W, and annealing to form a C54 TiSi_2 phase. In a different embodiment, Cabral deposits a

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Ti-Si alloy over the refractory metal. This alloy is targeted to be stoichiometric TiSi_2 , but may be richer or leaner in its silicon composition (See column 6, lines 4-17).

First, Applicant submits that, given the disparate problems faced by each of Maa, Cabral and the present invention, it would not have made it "obvious" to combine the references, absent impermissible hindsight construction of the present invention. Indeed, Cabral is trying to solve a different problem than Maa (let alone that addressed by the present invention as explained below).

Secondly, Cabral is not proposing a process which reduces silicon consumption. Cabral's proposes a method for forming the C54-TiSi_2 at a lower temperature than the conventional method, and preferably with one anneal.

Cabral is silent with respect to forming any of the intermediate silicon-rich phases. When annealing Ti over silicon, the following phases form with increased temperature:

$\text{Ti} \rightarrow \text{Ti}_3\text{Si} \rightarrow \text{Ti}_5\text{Si}_3 \rightarrow \text{Ti}_5\text{Si}_4 \rightarrow \text{TiSi} \rightarrow \text{C49-TiSi}_2 \rightarrow \text{C54-TiSi}_2$.

In contrast to Cabral, following the method of the present invention, one would first form a silicon-rich phase, such as the Ti_5Si_3 phase, etch the unreacted Ti, apply a silicon cap, and then run a second anneal to form the C54-TiSi_2 phase.

Cabral does not teach or suggest forming the Ti_5Si_3 phase or any other intermediate phase, but actually proposes a method that forms the final phase C54-TiSi_2 in one annealing step. Indeed, Cabral attempts to avoid the second "conversion-anneal". Cabral's process will

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preferably have one anneal step that will form the C54 TiSi_2 phase (See for example, column 2, lines 23-30, and column 6, lines 22-26).

Additionally, the embodiment in which Cabral proposes using a near stoichiometric TiSi_2 alloy, cannot be applied to the self-aligned silicide (SALICIDE) method.

The SALICIDE process includes applying a blanket metal film (such as Ti) onto a device structure (such as a MOSFET), annealing the wafer to react the metal with silicon surfaces to form a silicide (the metal over insulator surfaces, such as the MOSFET's sidewalls, does not convert into a silicide and remains a metal), etching the unreacted metal, and performing a second anneal to reach the desired silicide phase. The etching of the unreacted metal is essential to prevent bridging which otherwise will short the device source or drain area to the gate.

The above-described process is summarized in Cabral on column 1, line 47-55, and on column 11, line 48 to column 12, line 18. The etching is selective in the sense that it attacks the pure metal, but does not attack the silicide.

The SALICIDE process cannot be performed with a blanket deposited Ti - Silicon alloy (as opposed to Ti alloy, which is defined in Cabral as Ti with some refractory metal) having a composition of stoichiometric TiSi_2 , since the selective etch would no longer work. When a pure Ti or metallic Ti alloy is used, the metal over the device spacers does not convert into silicide during the anneal. Therefore, the unreacted metal can be etched since the etchant attacks only the metal, and does not remove silicide.

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In contrast, when a near stoichiometric Ti-Silicon alloy is blanket deposited, the spacers are covered with a Ti silicide the same as the rest of the device surfaces and the selectivity of metal versus silicide is lost. It is noted that this is precisely one of the reasons that Cabral specifies the refractive metal for forming the Ti alloy as being "preferably a metal that is capable of forming a metal silicide" (column 3, lines 65-66). In addition, Cabral describes the application of his invention to the SALICIDE method only with Ti alloy (column 11, lines 48-65).

Cabral is "skipping" the intermediate silicide phases. In contrast, Applicants are using a metal-containing silicon to extend the temperature window in which the silicide metal-rich phase exists. For example, this temperature window is extended from 20 °C to over 100 °C in the case of Co₂Si. This allows the invention to reliably form the metal-rich phase and apply the silicon cap as early as possible in the SALICIDE process. In complete and fundamental contrast, Cabral is trying to minimize the temperature window where the metal-rich silicide exists so that the final phase (C54-TiSi₂) will form at a lower temperature than that of the conventional method.

Thus, Applicants submit that Maa and Cabral would not have been combined by one of ordinary skill in the art at the time of the invention and absent hindsight.

Additionally, even assuming arguendo that Maa and Cabral would have been combined in the manner urged, the claimed invention would still not have been produced. Thus, claims 10 and 31-32 are patentable over the Examiner's proposed combination.

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IV. THE DOUBLE PATENTING REJECTIONS

With respect to the double patenting rejections, claims 1-8, 10-13 and 23-38 stand rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 28-31 of Ajmera et al. (U.S. Patent No. 6,503,833 B1).

However, Applicant has closely reviewed claims 28-31 of Ajmera et al. and submits that there are clear limitations found in claims 1-8, 10-13, and 23-38 which are not taught or suggested by claims 28-31 of Ajmera et al.

Indeed, Applicant submits that there is no teaching of suggestion by these claims of "depositing a metal containing silicon on a silicon substrate; reacting said metal containing silicon to form a first silicide phase; etching any unreacted metal containing silicon..." (Emphasis Applicant's), as in claim 1 and substantially similarly in independent claims 4, 13, 25, and 26. Again, Applicant points out to the Examiner that for a double patenting rejection, only the claims of the applied patent can be relied upon, not the disclosure. The Examiner cannot imaginatively read into the claims, limitations found only in the disclosure of the applied patent. Thus, here there are limitations in claims 1-8, 10-13, and 23-38 which are not taught or suggested by Ajmera et al.

Claims 1-50 of Cabral, Jr., et al. (U.S. Patent No. 6,444,578 B1) are similarly deficient.

Finally, the Examiner indicates that claims 1-8, 10-13, and 23-38 conflict with claims 1-30 of parent application No. 09/569,306. However, claims 1-30 of the copending application

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have been reviewed and clearly do not conflict with the present claims. Indeed, different inventions are being prosecuted and specifically methods directed to different inventive steps.

Indeed, Applicant submits that there is no teaching of suggestion by these copending claims 1-30 of "depositing a metal containing silicon alloy on a silicon substrate; reacting said metal containing silicon alloy to form a first silicide phase; etching any unreacted metal containing silicon..." as in claim 1 and substantially similarly in independent claims 10 and 16. Thus, the claims of the present application do not conflict with claims 1-30 of the patented and copending applications.

Notwithstanding the above, Applicant reserves the opportunity to file a Terminal Disclaimer at a later time.

In view of all of the foregoing, Applicant submits that all of the pending claims are patentable over the prior art of record.

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V. FORMAL MATTERS AND CONCLUSION

In view of the foregoing, Applicant submits that claims 1-8, 10-13 and 23-38, all the claims presently pending in the application, are patentably distinct over the prior art of record and are in condition for allowance. The Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

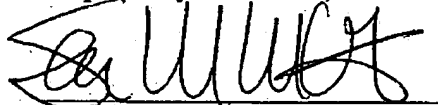
Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.

The Commissioner is hereby authorized to charge any deficiency in fees or to credit any overpayment in fees to Assignee's Deposit Account No. 50-0510.

Date:

11/24/03

Respectfully Submitted,



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CERTIFICATION OF FACSIMILE TRANSMISSION

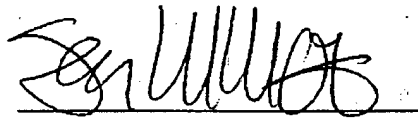
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Respectfully Submitted,

Date:

11/24/03



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THIRD COLLEGE EDITION

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Webster's New World
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EXHIBIT 1

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al-low (ə lou') *vt.* [ME *alowen* < OFr *alouer* < ML *allocare*, ALLO-CATE; assoc. with OFr *alouer* < L *allaudare*, to extol < *ad-*, to + *laudare*, to praise] 1 to let do, happen, etc.; permit; let [we weren't allowed to go] 2 to let have [she allowed herself no sweets] 3 to let enter or stay [dogs are not allowed] 4 to admit (a claim or the like); acknowledge as true or valid 5 to provide or allot (a certain amount, period of time, etc.) for a purpose [allow an inch for shrinkage] 6 [Dial.] a) to think; give as one's opinion b) to intend — **SYN.** LET — **allow for** to make allowance, provision, etc. for; keep in mind [allow for the difference in their ages] — **allow of** to be subject to; admit of

al-low-able (ə lou'ə bəl) *adj.* that can be allowed; permissible — **al-low-ably** *adv.*

al-low-ance (ə lou'əns) *n.* 1 the act of allowing, permitting, admitting, etc. [the allowance of a claim] 2 something allowed as a share; specif., an amount of money, food, etc. given regularly to a child, dependent, etc. or to military personnel for a specific purpose [travel allowance] 3 a reduction in the price of something in consideration of a large order or of turning in a used article, etc. 4 the amount by which something is allowed to be more or less than stated, as to compensate for the weight of the container, inaccuracy of machining, etc. — **vt.** -**anced**, -**ancing** 1 to put on an allowance or a ration 2 to apportion economically. — **adj.** designating a horse race in which the weight each horse must carry is set by a formula tied to the horse's past performance and earnings — **make allow-ance** (or **allowances**) to take circumstances, limitations, etc. into consideration — **make allowance** (or **allowances**) for 1 to forgive or excuse because of mitigating factors 2 to leave room, time, etc. for; allow for

al-low-ed-ly (ə lou'ld lē) *adv.* by allowance or admission; admittedly

al-loy (al'oi; also, and for *v.* usually, ə loi'; ə-) *n.* [ME *alai* < Anglo-Fr *alei* (OFr *aloi*) < *aleier*; see the *v.*] 1 the relative purity of gold or silver; fineness 2 a substance that is a mixture, as by fusion, of two or more metals, or of a metal and something else 3 a) a less valuable metal mixed with a more valuable one, often to give hard-ness b) something that lowers the value or quality of another thing when mixed with it — **vt.** [Fr *aloyer* < OFr *aloier*, *aleier* < L *alligare* < *ad-*, to + *ligare*, to bind; see LIGATURE] 1 to make (a metal) less pure by mixing with a less valuable metal 2 to mix (metals) to form an alloy 3 to debase by mixing with something inferior

all-purpose (əl'par'pəs) *adj.* for every pertinent purpose; useful in many ways

all right (əl rit'; əl'rit', əl'rit') 1 satisfactory; adequate 2 unhurt; safe 3 correct 4 yes; very well: used in reply to a question or merely to preface or resum. one's remarks 5 [Colloq.] certainly [h 's the one who did it, all right]

all-right (əl'rit', əl'rit', əl rit') *adj.* [Slang] honest, honorable; good, excellent, etc.: used before the noun it modifies

all-round (əl'round', əl'round') *adj., adv.* var. of ALL-AROUND

All Saints' Day an annual church festival (Nov. 1) in honor of all